TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

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COLOR TV VERT. DEFLECTION OUTPUT APPLICATIONS.

COLOR TV CLASS B SOUND OUTPUT APPLICATIONS.

- Large Collector Current and Collector Power Dissipation Capability.
- Recommended for Vert. Deflection Output and Sound Output Applications for Line Operated TV.
- Complementary to 2SA1408.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT	
Collector-Base Voltage		v_{CBO}	150	V	
Collector-Emitter Voltage		v_{CEO}	150	V	
Emitter-Base Voltage		$v_{ m EBO}$	6	V	
Collector Current		$I_{\mathbf{C}}$	1.5	Α	
Base Current		$I_{\mathbf{B}}$	1.0	Α	
Collector Power	Ta = 25°C	$P_{\mathbf{C}}$	1.5	w	
Dissipation	$Tc = 25^{\circ}C$	1 C	10		
Junction Temperature		$\mathrm{T_{j}}$	150	$^{\circ}\mathrm{C}$	
Storage Temperature Range		$\mathrm{T_{stg}}$	-55~150	°C	

1. EMITTER
2. COLLECTOR
3. BASE

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EIAJ

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Unit in mm

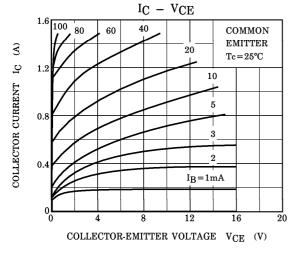
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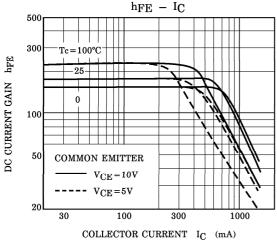
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

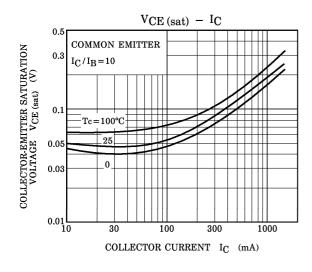
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	$V_{CB} = 150V, I_E = 0$	_	_	1.0	μ A
Emitter Cut-off Current	$I_{ m EBO}$	$V_{EB}=6V, I_{C}=0$	_	_	1.0	μ A
Collector-Emitter Breakdown Voltage	V (BR) CEO	$I_{\rm C}$ =10mA, $I_{\rm B}$ =0	150	_	_	V
DC Current Gain	hFE (Note)	$V_{\rm CE}$ =5V, $I_{\rm C}$ =200mA	60	_	200	
Collector-Emitter Saturation Voltage	V _{CE} (sat)	I _C =500mA, I _B =50mA	_	_	1.5	V
Base-Emitter Voltage	$ m V_{BE}$	$V_{CE}=5V$, $I_{C}=5mA$	0.5	_	0.8	V
Transition Frequency	$ m f_{T}$	$V_{ m CE}$ =5V, I $_{ m C}$ =200mA	20	100	_	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 10V, I_{E} = 0, f = 1MHz$	_	13	20	рF

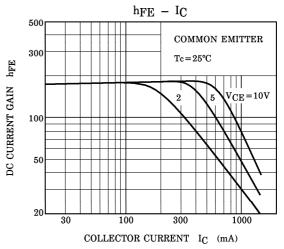
Note: hFE Classification R: 60~120, O: 100~200

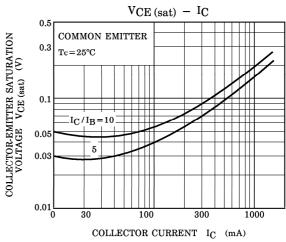
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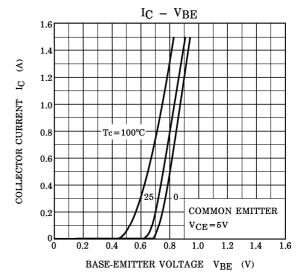




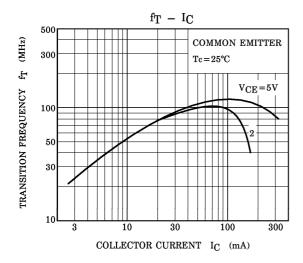


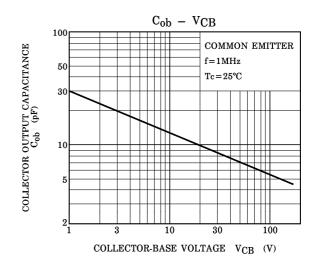


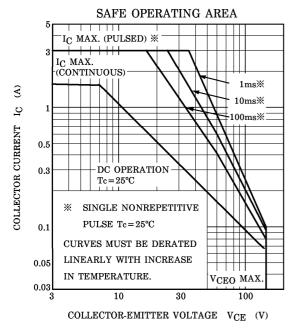




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